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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I ² S, POR, PWM, WDT
Number of I/O	83
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	12K x 8
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	104-UFBGA, WLCSP
Supplier Device Package	104-WLCSP (5.09x4.1)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151vdy6xtr

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- **Stop mode without RTC**

Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8 μ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

- **Standby mode with RTC**

Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in 60 μ s when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 2. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation
$V_{DD} = V_{DDA} = 1.65$ to 1.71 V	Not functional	Not functional	Range 2 or Range 3	Degraded speed performance
$V_{DD} = V_{DDA} = 1.71$ to 1.8 V ⁽¹⁾	Not functional	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance
$V_{DD} = V_{DDA} = 1.8$ to 2.0 V	Conversion time up to 500 Ksps	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance

Table 4. Functionalities depending on the working mode (from Run/active down to standby) (continued)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
ADC	Y	Y	--	--	--	--	--	--
DAC	Y	Y	Y	Y	Y	--	--	--
Tempsensor	Y	Y	Y	Y	Y	--	--	--
OP amp	Y	Y	Y	Y	Y	--	--	--
Comparators	Y	Y	Y	Y	Y	Y	--	--
16-bit and 32-bit Timers	Y	Y	Y	Y	--	--	--	--
IWDG	Y	Y	Y	Y	Y	Y	Y	Y
WWDG	Y	Y	Y	Y	--	--	--	--
Touch sensing	Y	Y	--	--	--	--	--	--
Systic Timer	Y	Y	Y	Y		--	--	--
GPIOs	Y	Y	Y	Y	Y	Y	--	3 pins
Wakeup time to Run mode	0 μ s	0.4 μ s	3 μ s	46 μ s	< 8 μ s		58 μ s	
Consumption $V_{DD}=1.8$ to 3.6 V (Typ)	Down to 195 μ A/MHz (from Flash)	Down to 38 μ A/MHz (from Flash)	Down to 11 μ A	Down to 4.6 μ A	0.53 μ A (no RTC) $V_{DD}=1.8$ V		0.285 μ A (no RTC) $V_{DD}=1.8$ V	
					1.2 μ A (with RTC) $V_{DD}=1.8$ V		0.97 μ A (with RTC) $V_{DD}=1.8$ V	
					0.56 μ A (no RTC) $V_{DD}=3.0$ V		0.29 μ A (no RTC) $V_{DD}=3.0$ V	
					1.4 μ A (with RTC) $V_{DD}=3.0$ V		1.11 μ A (with RTC) $V_{DD}=3.0$ V	

1. The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

3.2 ARM[®] Cortex[®]-M3 core with MPU

The ARM[®] Cortex[®]-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM[®] Cortex[®]-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wake-up logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot from Flash usually boots at the beginning of the Flash (bank 1). An additional boot mechanism is available through user option byte, to allow booting from bank 2 when bank 2 contains valid code. This dual boot capability can be used to easily implement a secure field software update mechanism.

The boot loader is located in System memory. It is used to reprogram the Flash memory by using USART1, USART2 or USB. See Application note "STM32 microcontroller system memory boot mode" (AN2606) for details.

3.17.3 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

3.17.4 Inter-integrated sound (I²S)

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The I2Ss can be served by the DMA controller.

3.17.5 Universal serial bus (USB)

The STM32L151VD-X and STM32L152VD-X devices embed a USB device peripheral compatible with the USB full-speed 12 Mbit/s. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

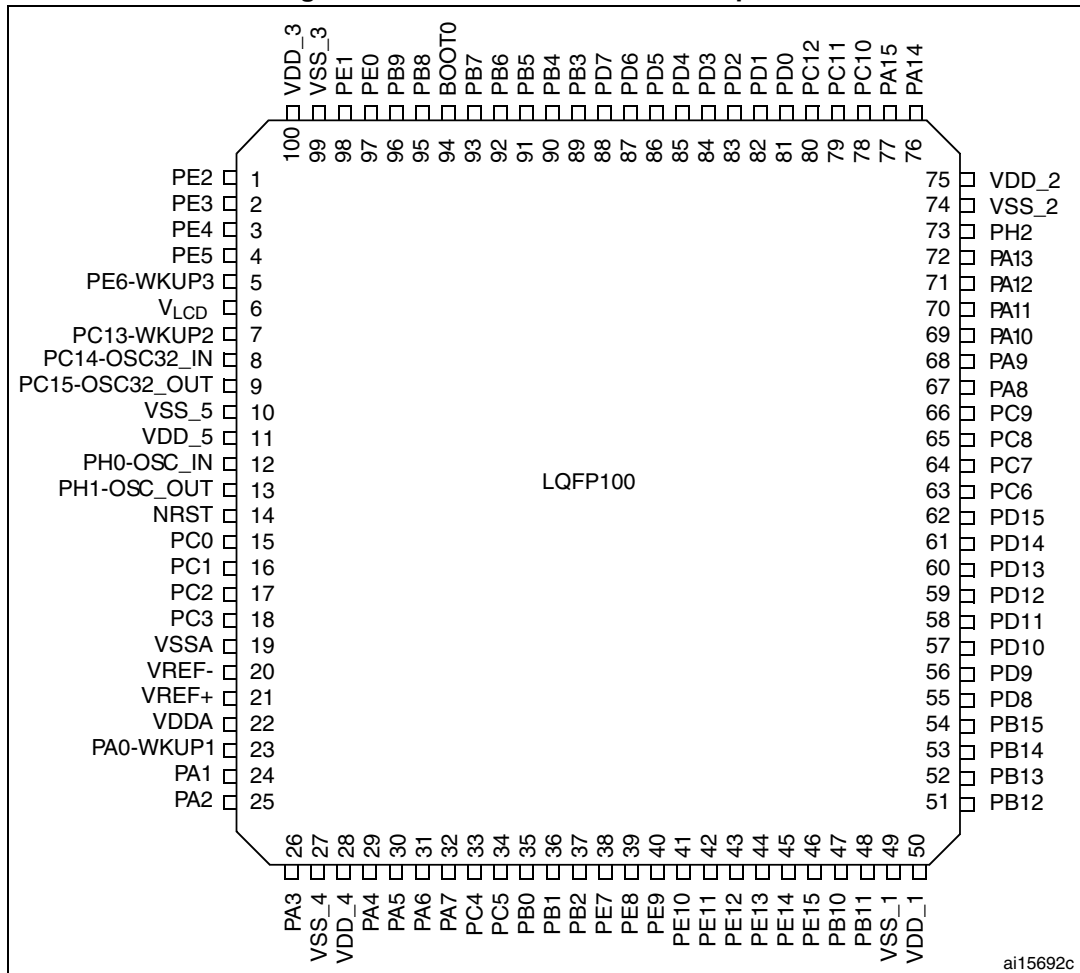
3.18 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

4 Pin descriptions

Figure 3. STM32L152VD-X LQFP100 pinout



1. This figure shows the package top view.

Table 6. Legend/abbreviations used in the pinout table (continued)

Name		Abbreviation	Definition
Notes			Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset
Pin functions	Alternate functions		Functions selected through GPIOx_AFR registers
	Additional functions		Functions directly selected/enabled through peripheral registers

Table 7. STM32L151VD-X and STM32L152VD-X pin definitions

Pins		Pin name	Pin Type ⁽¹⁾	I / O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP100	WLCSP104					Alternate functions	Additional functions
1	D6	PE2	I/O	FT	PE2	TIM3_ETR/LCD_SEG38/ TRACECLK	-
2	D7	PE3	I/O	FT	PE3	TIM3_CH1/LCD_SEG39/ TRACED0	-
3	C8	PE4	I/O	FT	PE4	TIM3_CH2/TRACED1	-
4	B9	PE5	I/O	FT	PE5	TIM9_CH1/TRACED2	-
5	E6	PE6- WKUP3	I/O	FT	PE6	TIM9_CH2/TRACED3	WKUP3/ RTC_TAMP3
6	E7	V _{LCD} ⁽³⁾	S	-	V _{LCD}	-	-
7	C9	PC13-WKUP2	I/O	FT	PC13	-	WKUP2/RTC_TA MP1/RTC_TS/ RTC_OUT
8	D8	PC14- OSC32_IN ⁽⁴⁾	I/O	TC	PC14	-	OSC32_IN
9	D9	PC15- OSC32_OUT	I/O	TC	PC15	-	OSC32_OUT
10	E8	V _{SS_5}	S		V _{SS_5}	-	-
11	E9	V _{DD_5}	S		V _{DD_5}	-	-
12	F8	PH0-OSC_IN ⁽⁵⁾	I/O	TC	PH0	-	OSC_IN
13	F9	PH1- OSC_OUT ⁽⁵⁾	I/O	TC	PH1	-	OSC_OUT
14	F7	NRST	I/O	RST	NRST	-	-

Table 7. STM32L151VD-X and STM32L152VD-X pin definitions (continued)

Pins		Pin name	Pin Type ⁽¹⁾	I / O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP100	WLCSP104					Alternate functions	Additional functions
63	H1	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/ LCD_SEG24	-
64	G1	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25	-
65	G2	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
66	F4	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
67	F3	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
68	F1	PA9	I/O	FT	PA9	USART1_TX / LCD_COM1	-
69	F2	PA10	I/O	FT	PA10	USART1_RX / LCD_COM2	-
70	E1	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
71	E2	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
72	E3	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
73	D1	PH2	I/O	FT	PH2	-	-
74	D2, A1	V _{SS_2}	S	-	V _{SS_2}	-	-
75	C1	V _{DD_2}	S	-	V _{DD_2}	-	-
76	D3	PA14	I/O	FT	JTCK-SWCLK	JTCK-SWCLK	-
77	B1	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/ SPI1_NSS/SPI3_NSS/ I2S3_WS/LCD_SEG17/ JTDI	-
78	E4	PC10	I/O	FT	PC10	SPI3_SCK/I2S3_CK/ USART3_TX/UART4_TX/ LCD_SEG28/ LCD_SEG40/LCD_COM4	-



Table 8. Alternate function input/output (continued)

Port name	Digital alternate function number											
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	AFIO11	AFIO14	AFIO15
	Alternate function											
	SYSTEM	TIM2	TIM3/4/ 5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/ 3	UART4/ 5	LCD	CPRI	SYSTEM
PD4	-	-	-	-	-	SPI2_MOSI I2S2_SD	-	USART2_RTS	-	-	-	TIMx_IC1 EVENT OUT
PD5	-	-	-	-	-	-	-	USART2_TX	-	-	-	TIMx_IC2 EVENT OUT
PD6	-	-	-	-	-	-	-	USART2_RX	-	-	-	TIMx_IC3 EVENT OUT
PD7	-	-	-	TIM9_CH2	-	-	-	USART2_CK	-	-	-	TIMx_IC4 EVENT OUT
PD8	-	-	-	-	-	-	-	USART3_TX	-	SEG28	-	TIMx_IC1 EVENT OUT
PD9	-	-	-	-	-	-	-	USART3_RX	-	SEG29	-	TIMx_IC2 EVENT OUT
PD10	-	-	-	-	-	-	-	USART3_CK	-	SEG30	-	TIMx_IC3 EVENT OUT
PD11	-	-	-	-	-	-	-	USART3_CTS	-	SEG31	-	TIMx_IC4 EVENT OUT
PD12	-	-	TIM4_CH1	-	-	-	-	USART3_RTS	-	SEG32	-	TIMx_IC1 EVENT OUT
PD13	-	-	TIM4_CH2	-	-	-	-	-	-	SEG33	-	TIMx_IC2 EVENT OUT
PD14	-	-	TIM4_CH3	-	-	-	-	-	-	SEG34	-	TIMx_IC3 EVENT OUT
PD15	-	-	TIM4_CH4	-	-	-	-	-	-	SEG35	-	TIMx_IC4 EVENT OUT
PE0	-	-	TIM4_ETR	TIM10_CH1	-	-	-	-	-	SEG36	-	TIMx_IC1 EVENT OUT
PE1	-	-	-	TIM11_CH1	-	-	-	-	-	SEG37	-	TIMx_IC2 EVENT OUT



Table 8. Alternate function input/output (continued)

Port name	Digital alternate function number											
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	AFIO11	AFIO14	AFIO15
	Alternate function											
	SYSTEM	TIM2	TIM3/4/ 5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/ 3	UART4/ 5	LCD	CPRI	SYSTEM
PF0	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF1	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF2	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF3	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF4	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF5	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF6	-	-	TIM5_ETR	-	-	-	-	-	-	-	-	EVENT OUT
PF7	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	EVENT OUT
PF8	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	EVENT OUT
PF9	-	-	TIM5_CH4	-	-	-	-	-	-	-	-	EVENT OUT
PF10	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF11	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF12	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PF13	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

- Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 9](#) for maximum allowed input voltage values.
- A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 9: Voltage characteristics](#) for the maximum allowed input voltage values.
- When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 11. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 12. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
$V_{DDA}^{(1)}$	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as $V_{DD}^{(2)}$	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
V_{IN}	I/O input voltage	FT pins; $2.0\text{ V} \leq V_{DD}$	-0.3	5.5 ⁽³⁾	V
		FT pins; $V_{DD} < 2.0\text{ V}$	-0.3	5.25 ⁽³⁾	
		BOOT0 pin	0	5.5	
		Any other pin	-0.3	$V_{DD} + 0.3$	
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽⁴⁾	LQFP100 package	-	465	mW
		WLCSP104 package	-	435	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation ⁽⁵⁾	-40	85	°C
	Ambient temperature for 7 suffix version	Maximum power dissipation	-40	105	
T_J	Junction temperature range	6 suffix version	-40	105	°C
		7 suffix version	-40	110	

1. When the ADC is used, refer to [Table 54: ADC characteristics](#).

Table 13. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	V
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.

2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Table 16. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	225	500	μA
				2 MHz	420	750	
				4 MHz	780	1200	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.98	1.6	mA
				8 MHz	1.85	2.9	
				16 MHz	3.6	5.2	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	2.2	3.5	
				16 MHz	4.4	6.5	
				32 MHz	8.6	12	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	3.6	5.2	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	8.7	12.3	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	42	145	μA
		MSI clock, 524 kHz		524 kHz	135	250	
		MSI clock, 4.2 MHz		4.2 MHz	820	1200	

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 17. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	1 MHz	200	470	μA
				2 MHz	360	780	
				4 MHz	685	1200	
			Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	4 MHz	0.80	1.5	mA
				8 MHz	1.6	3	
				16 MHz	3.1	5	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	8 MHz	1.9	3.5	
				16 MHz	3.7	5.55	
				32 MHz	7.55	10.9	
		HSI clock source (16 MHz)	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	16 MHz	3.15	4.8	
			Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	32 MHz	7.75	11.7	
		MSI clock, 65 kHz	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	65 kHz	40	130	μA
		MSI clock, 524 kHz		524 kHz	115	215	
		MSI clock, 4.2 MHz		4.2 MHz	715	1100	

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

6.3.7 Internal clock source characteristics

The parameters given in [Table 29](#) are derived from tests performed under the conditions summarized in [Table 12](#).

High-speed internal (HSI) RC oscillator

Table 29. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	$V_{\text{DD}} = 3.0 \text{ V}$	-	16	-	MHz
$\text{TRIM}^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
$\text{ACC}_{\text{HSI}}^{(2)}$	Accuracy of the factory-calibrated HSI oscillator	$V_{\text{DDA}} = 3.0 \text{ V}, T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$	-1 ⁽³⁾	-	1 ⁽³⁾	%
		$V_{\text{DDA}} = 3.0 \text{ V}, T_{\text{A}} = 0 \text{ to } 55 \text{ }^{\circ}\text{C}$	-1.5	-	1.5	%
		$V_{\text{DDA}} = 3.0 \text{ V}, T_{\text{A}} = -10 \text{ to } 70 \text{ }^{\circ}\text{C}$	-2	-	2	%
		$V_{\text{DDA}} = 3.0 \text{ V}, T_{\text{A}} = -10 \text{ to } 85 \text{ }^{\circ}\text{C}$	-2.5	-	2	%
		$V_{\text{DDA}} = 3.0 \text{ V}, T_{\text{A}} = -10 \text{ to } 105 \text{ }^{\circ}\text{C}$	-4	-	2	%
		$V_{\text{DDA}} = 1.65 \text{ V to } 3.6 \text{ V}$ $T_{\text{A}} = -40 \text{ to } 105 \text{ }^{\circ}\text{C}$	-4	-	3	%
$t_{\text{SU(HSI)}}^{(2)}$	HSI oscillator startup time	-	-	3.7	6	μs
$I_{\text{DD(HSI)}}^{(2)}$	HSI oscillator power consumption	-	-	100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Low-speed internal (LSI) RC oscillator

Table 30. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$f_{\text{LSI}}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{\text{LSI}}^{(2)}$	LSI oscillator frequency drift $0^{\circ}\text{C} \leq T_{\text{A}} \leq 105^{\circ}\text{C}$	-10	-	4	%
$t_{\text{SU(LSI)}}^{(3)}$	LSI oscillator startup time	-	-	200	μs
$I_{\text{DD(LSI)}}^{(3)}$	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

Table 31. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{\text{STAB(MSI)}}^{(2)}$	MSI oscillator stabilization time	MSI range 0	-	40	μs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{\text{OVER(MSI)}}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results.

6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB: A Burst of Fast Transient voltage** (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 36](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 36. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 32\text{ MHz}$ conforms to IEC 61000-4-2	4B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 32\text{ MHz}$ conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

6.3.22 LCD controller

The device embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 63. LCD controller characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V_{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V_{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V_{LCD3}	LCD internal reference voltage 3	-	2.98	-	
V_{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V_{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V_{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V_{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C_{ext}	V_{LCD} external capacitance	0.1	-	2	μF
$I_{LCD}^{(1)}$	Supply current at $V_{DD} = 2.2 V$	-	3.3	-	μA
	Supply current at $V_{DD} = 3.0 V$	-	3.1	-	
$R_{Htot}^{(2)}$	Low drive resistive network overall value	5.28	6.6	7.92	$M\Omega$
$R_L^{(2)}$	High drive resistive network total value	192	240	288	$k\Omega$
V_{44}	Segment/Common highest level voltage	-	-	V_{LCD}	V
V_{34}	Segment/Common 3/4 level voltage	-	$3/4 V_{LCD}$	-	V
V_{23}	Segment/Common 2/3 level voltage	-	$2/3 V_{LCD}$	-	
V_{12}	Segment/Common 1/2 level voltage	-	$1/2 V_{LCD}$	-	
V_{13}	Segment/Common 1/3 level voltage	-	$1/3 V_{LCD}$	-	
V_{14}	Segment/Common 1/4 level voltage	-	$1/4 V_{LCD}$	-	
V_0	Segment/Common lowest level voltage	0	-	-	
$\Delta V_{xx}^{(3)}$	Segment/Common level voltage error $T_A = -40$ to $105^\circ C$	-	-	± 50	mV

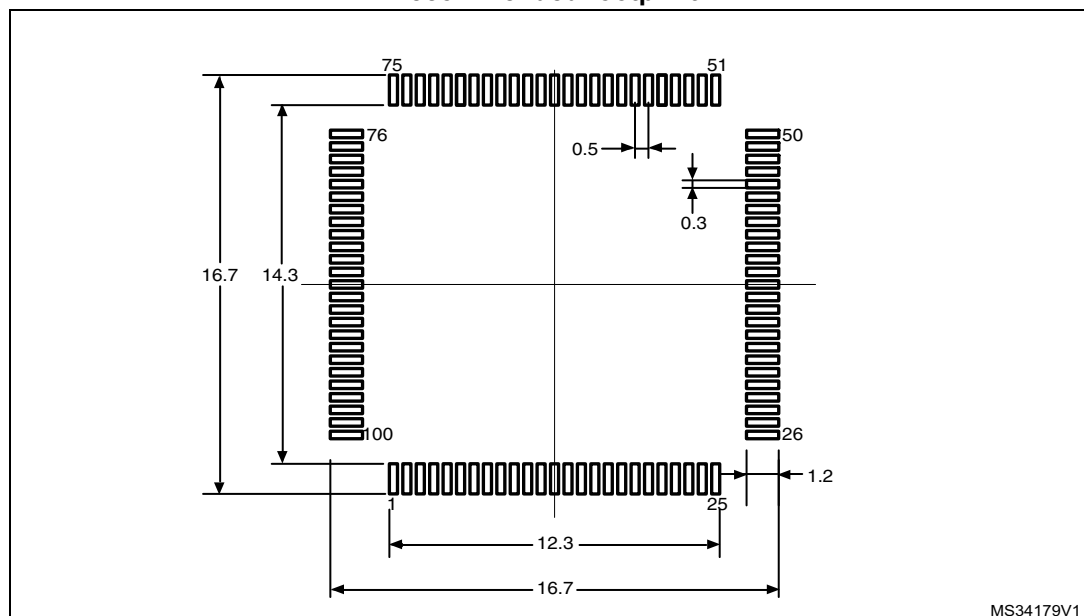
1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.
2. Guaranteed by design.
3. Guaranteed by characterization results.

Table 64. LQPF100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 29. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.